

Fig. 1 (a)

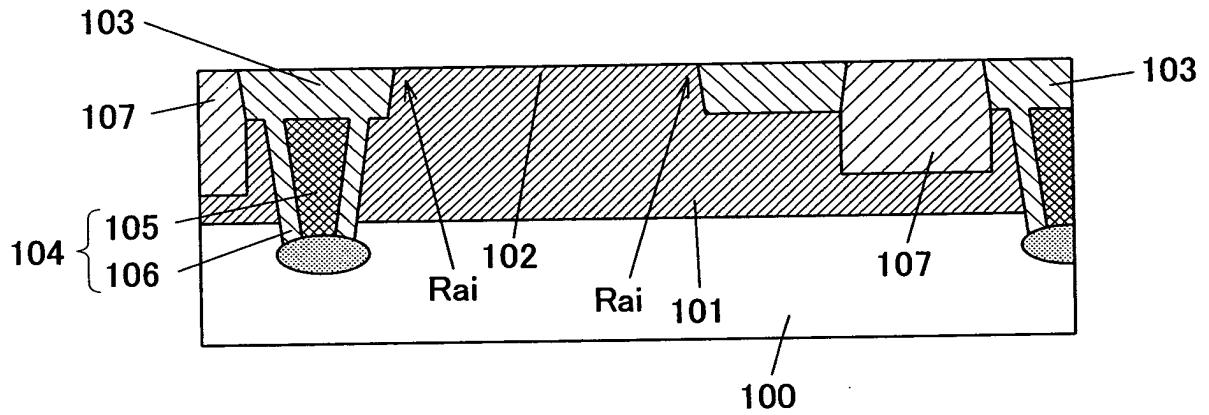


Fig. 1 (b)

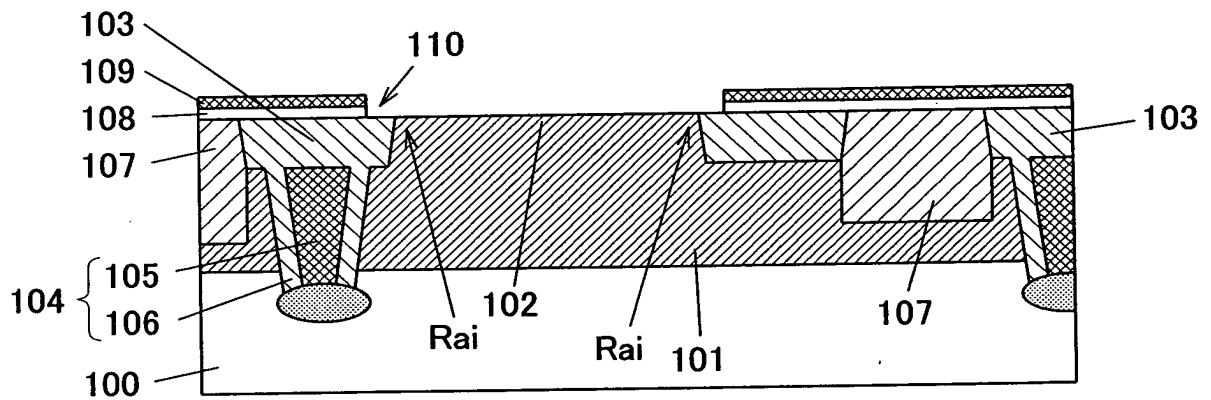


Fig. 1 (c)

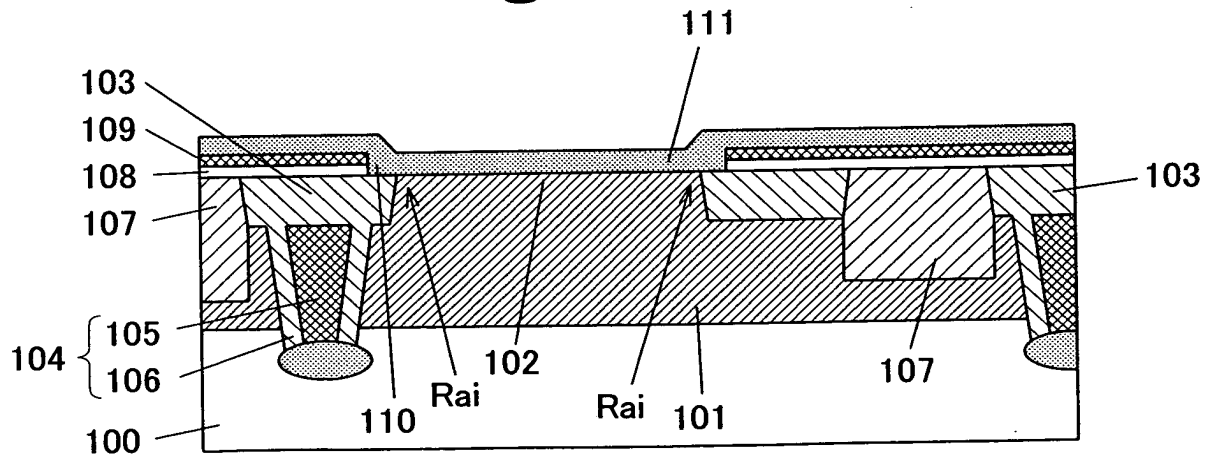


Fig. 2(d)

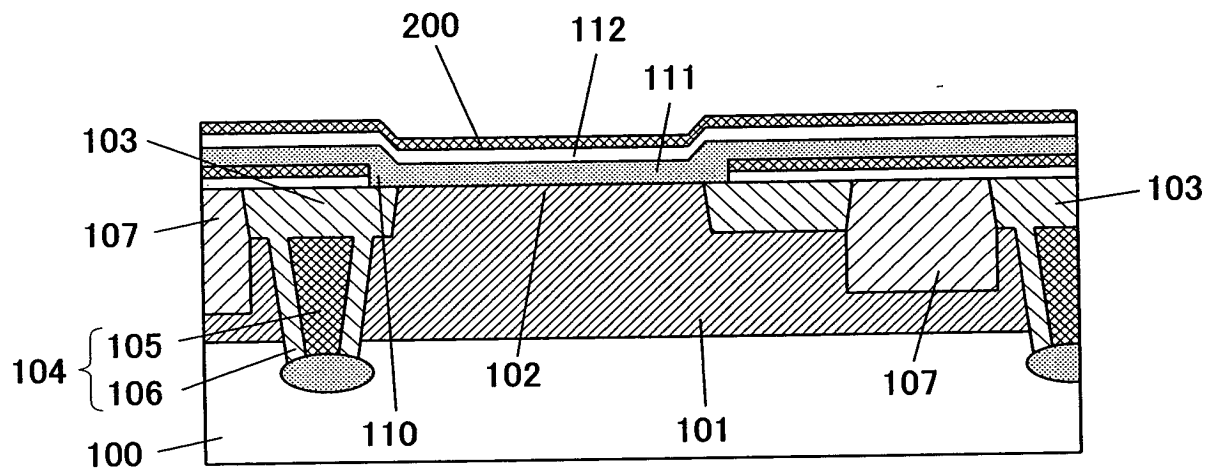


Fig. 2(e)

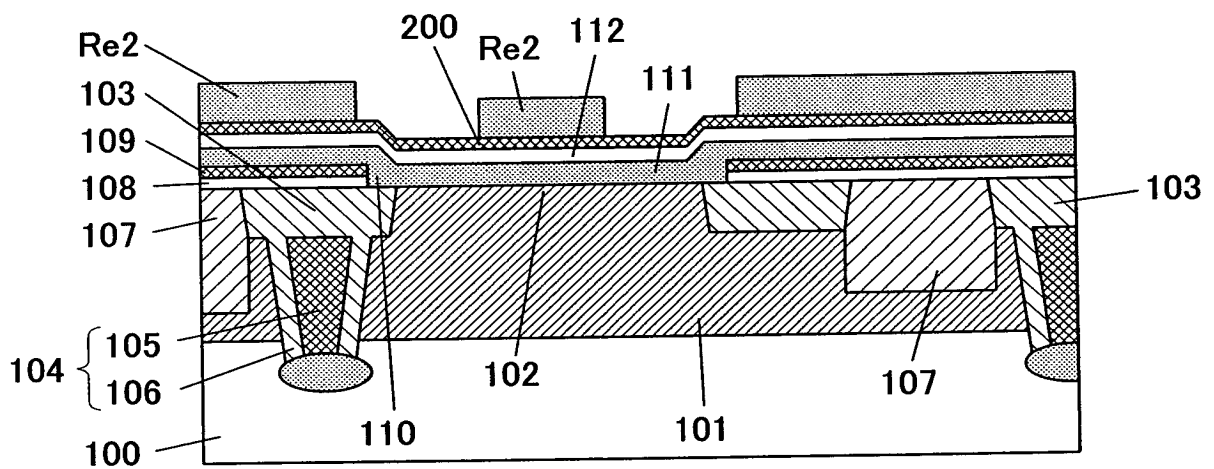
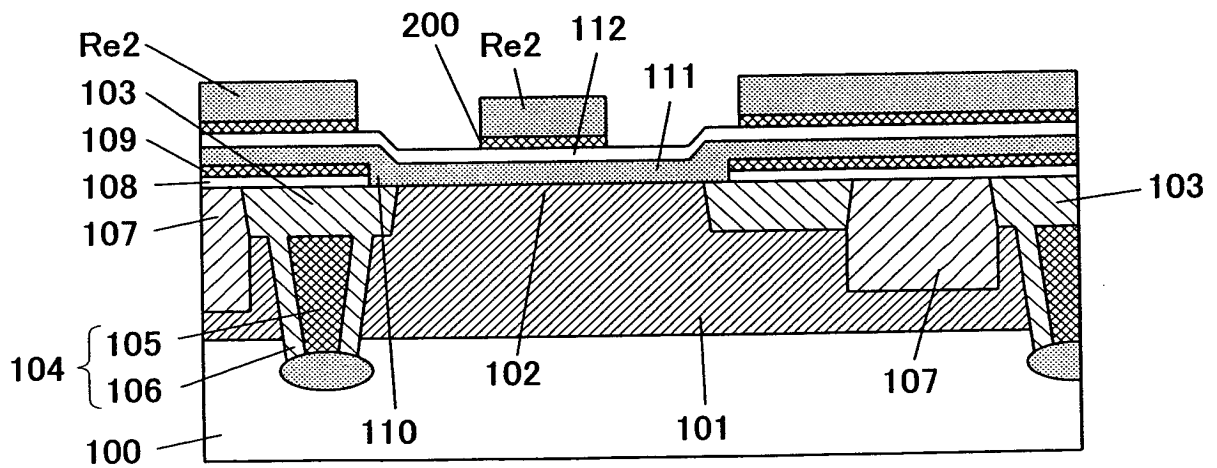
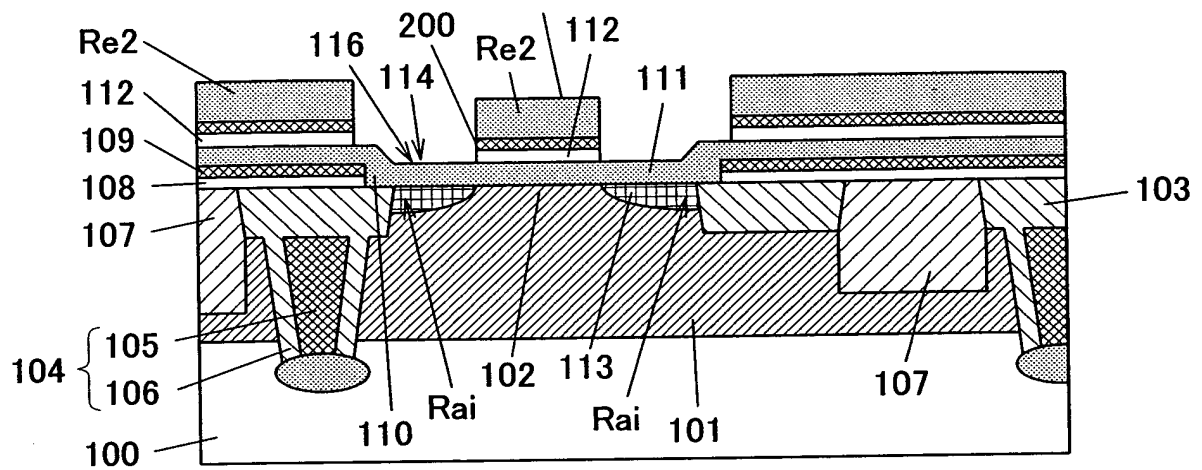


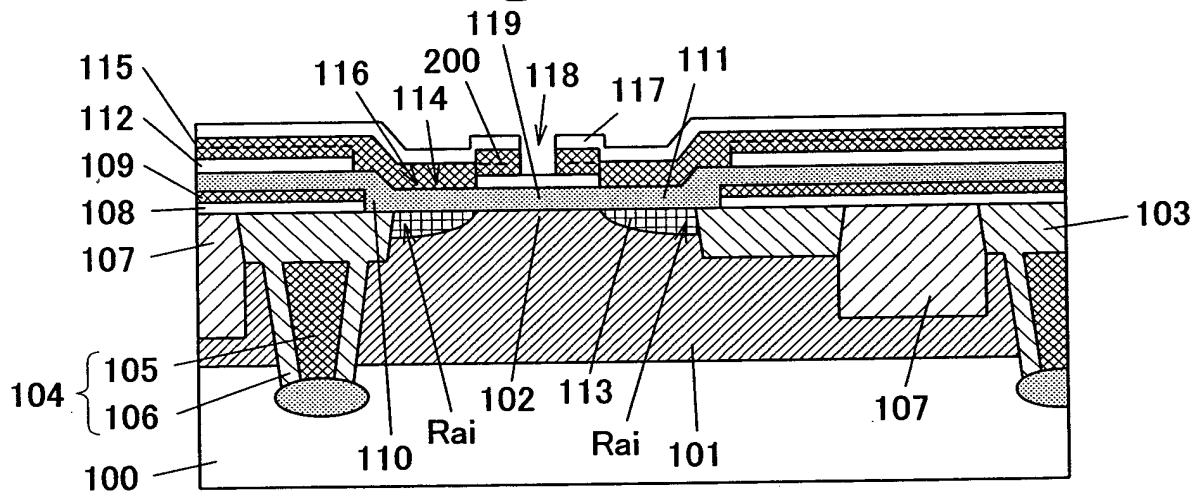
Fig. 2(f)



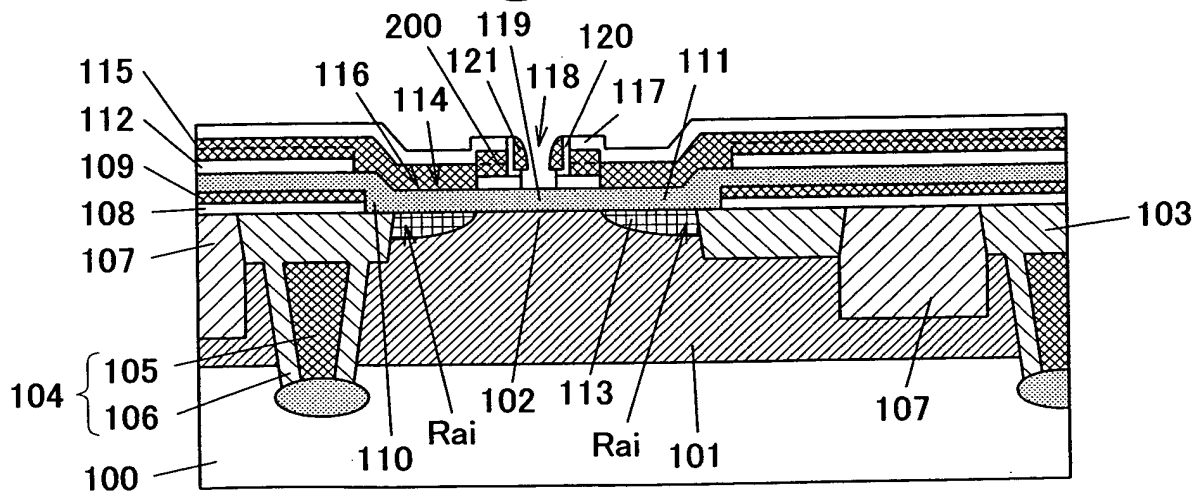
i



119



119



[illegible]

Fig. 1 is a cross-sectional view of a semiconductor device. The device is built on a substrate 100. A base layer 101 is formed on the substrate. A patterned layer 102 is formed on the base layer, with a central region 110 and side regions 105 and 106. A top layer 103 is formed on the patterned layer. The central region 110 contains a structure 111. The side regions 105 and 106 contain structures 105 and 106, respectively. Various layers and features are labeled with numbers 100 through 119.

[illegible]

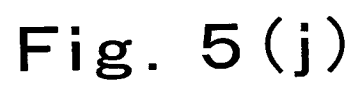


Fig. 5 (j)

Fig. 6(a) PRIOR ART

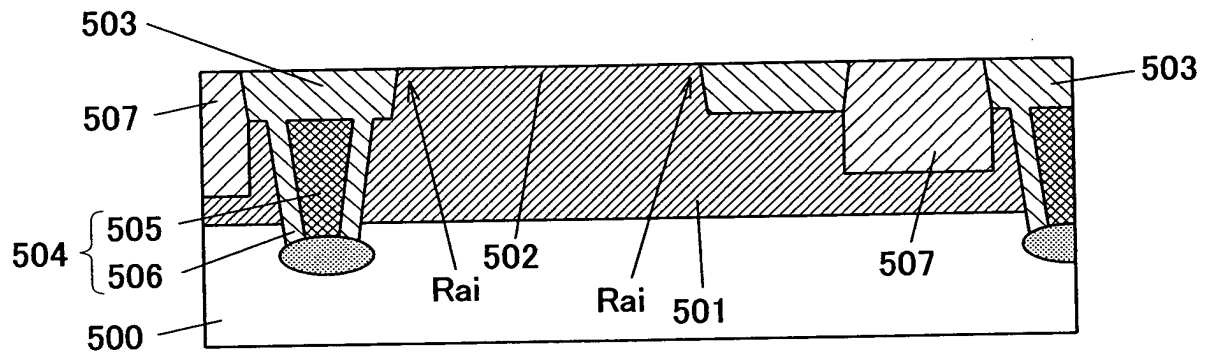


Fig. 6(b) PRIOR ART

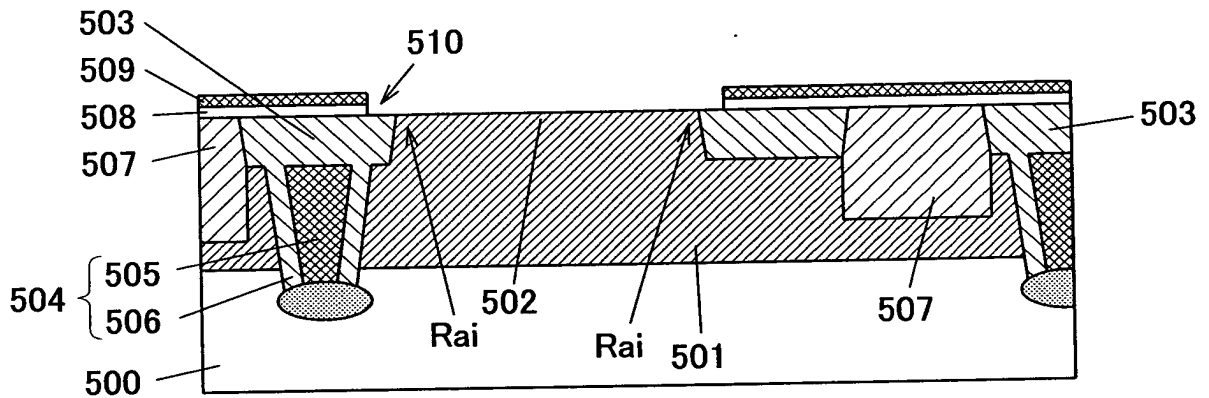


Fig. 6(c) PRIOR ART

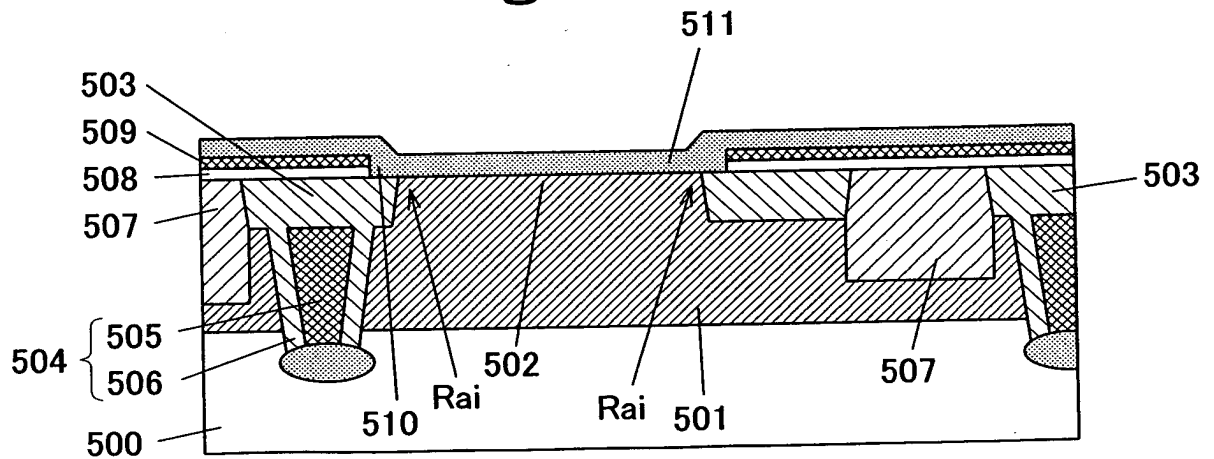


Fig. 7(d) PRIOR ART

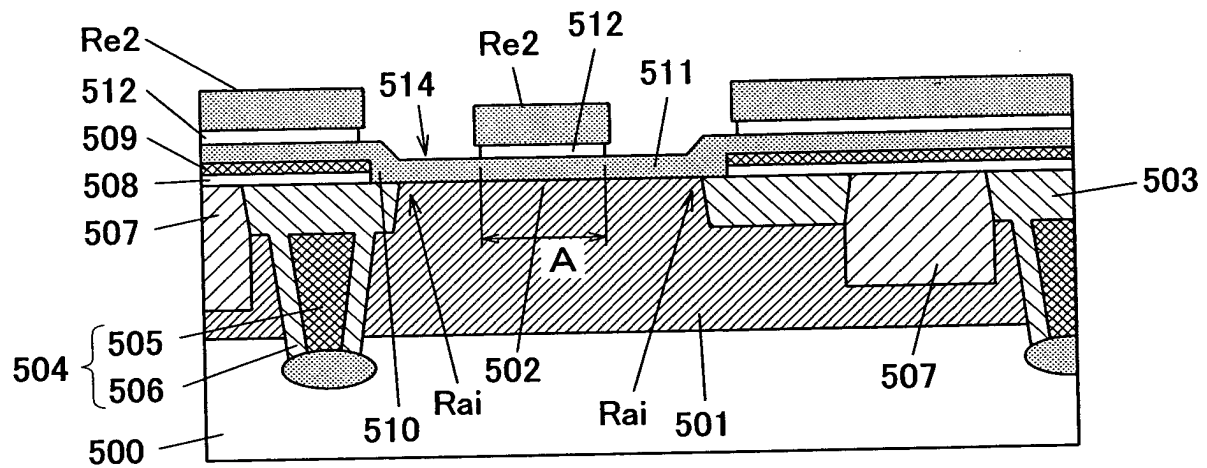


Fig. 7(e) PRIOR ART

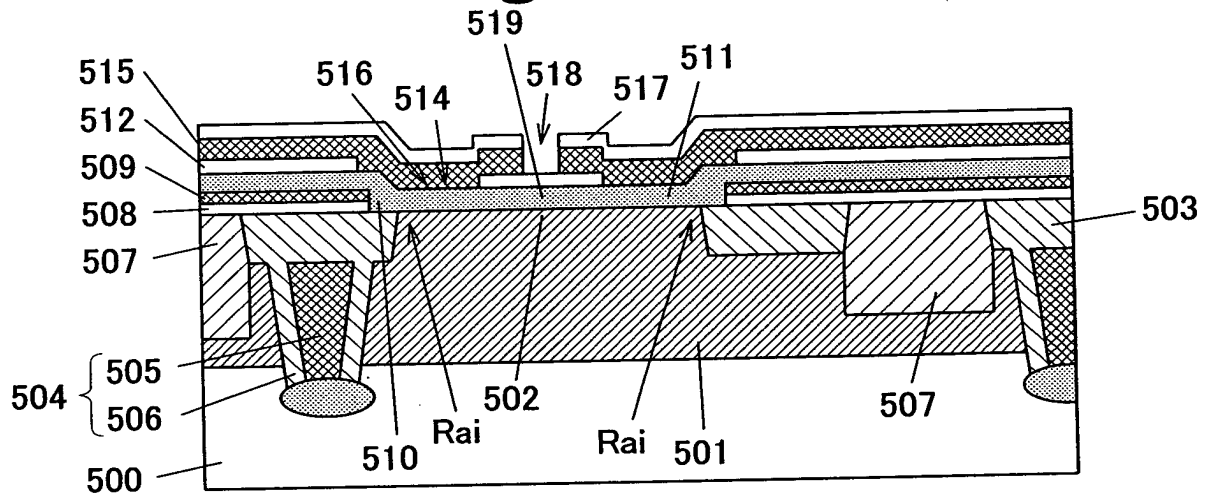
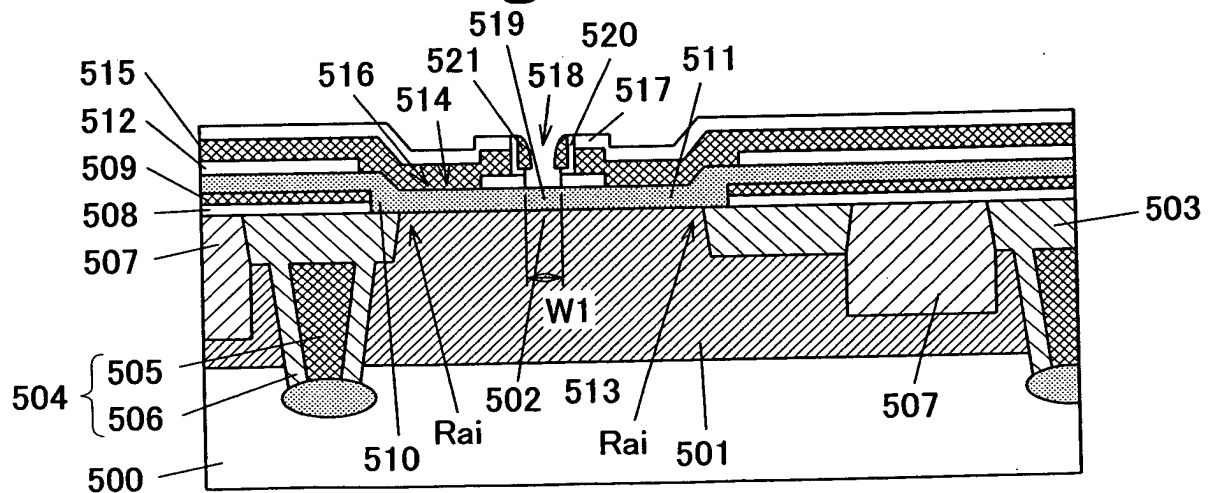


Fig. 7(f) PRIOR ART



[illegible][illegible][illegible]

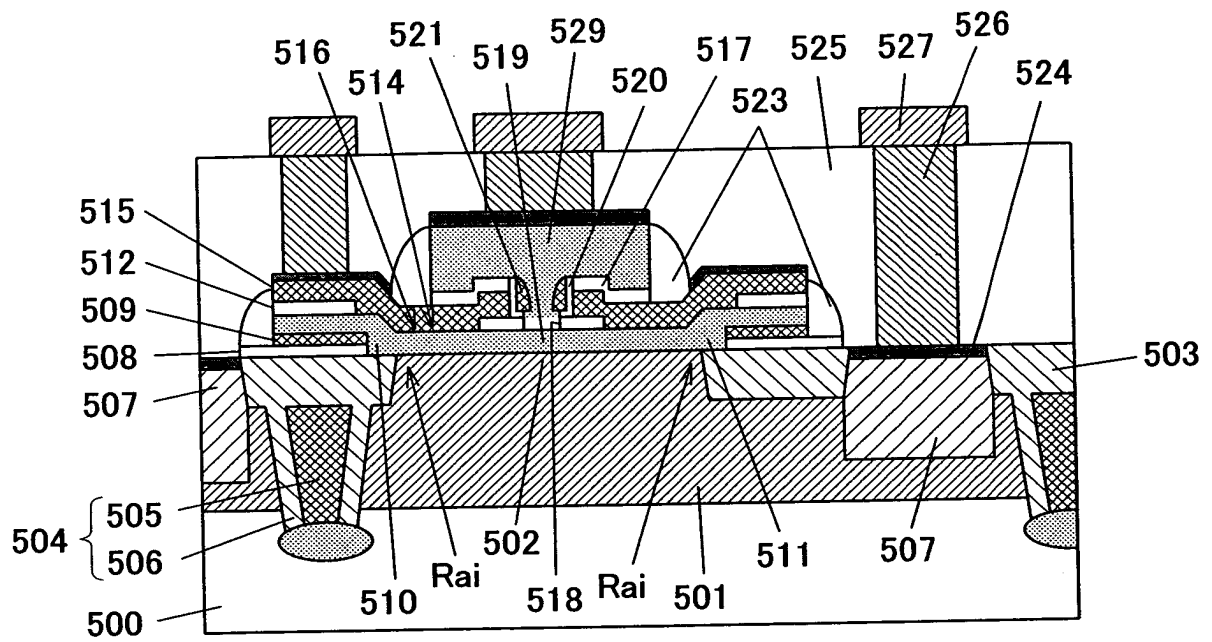


Fig. 9(j) PRIOR ART